

WHAT IS CLAIMED IS:

1. A semiconductor device comprising:
a semiconductor member having thereon a plurality
of interconnect pads: and

a mounting member having a plurality of electrode

- 5 terminals electrically and mechanically connected to the
respective interconnect pads for mounting the
semiconductor chip on the mounting member,

the electrode terminals forming a plurality of I/O
cells each having part of the electrode terminals, the part
10 of electrode terminals including signal terminals, the I/O
cells forming a first group of the I/O cells and a second
group of I/O cells disposed on an inner position of the
mounting member with respect to the first group.

- R there
2 chips 2
1/2, 2nd*
2. The semiconductor device as defined in claim 1,
wherein the semiconductor member is a semiconductor
chip, the electrode terminals are internal electrodes
disposed on a bottom surface of the semiconductor chip,
and the mounting member is a package substrate used
for packaging thereon the semiconductor chip.

- A*
3. The semiconductor device as defined in claim 1,

wherein the mounting member is a semiconductor package mounting a semiconductor chip on a packaging substrate, the electrode terminals are ball electrodes disposed on a bottom surface of the packaging substrate, and the substrate is a mounting substrate for forming a specified circuit by mounting the semiconductor package thereon.

4. The semiconductor device as defined in claim 1,
^(c)
 wherein the I/O cell includes only the electrode terminals for signals or the electrode terminals for signals, power and ground intermingled among one another.

112, 2nd 5. The semiconductor device as defined in claim 4,
^(c)
 wherein the I/O cell includes peripherals. *func if the cell is one in the periphery*

112, 2nd 6. The semiconductor device as defined in claim 1,
^{is it}
^{one line or}
^{a plurality}
^{of lines?}
 wherein an interconnect line is connected to the interconnect pads, and the interconnect lines connected to the interconnect pad of the at least one of the I/O cells are formed in a single interconnect layer.

Same of 6
 Same of 6
 7. The semiconductor device as defined in claim 6,
 wherein the substrate includes the interconnect pads and
^{an electric}
^{the interconnect} line ^{or lines} electrically connected to the
 112, 2nd

interconnect pads in the single interconnect layer formed
 5 on the surface of the substrate.

8. The semiconductor device as defined in claim 7,
 wherein the interconnect lines connected to the I/O cells
 located on inner positions extend between the I/O cells
 located on the outer periphery.
an

9. The semiconductor device as defined in claim 6,
 wherein the interconnect pads and the interconnect lines *R the pads
on the line
formed as
a multi-layered
interconnect
layer?*
 electrically connected to the interconnect pads are formed as a multi-layered interconnect layer in the substrate.

10. The semiconductor device as defined in claim 9,
 wherein at least one of the first group and the second
 group includes an outer group and an inner group
 disposed on the inner position of the mounting member
 with respect to the outer group. *ok, sec claim 1*

11. The semiconductor device as defined in claim 10,
 wherein the interconnect lines connected to the *obj red* ^{group of the} interconnect pads corresponding to the first I/O cells and
 the interconnect lines connected to the interconnect pads
 5 corresponding to the second I/O cells are formed in different interconnect layers.